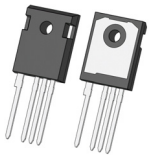
Silicon Carbide (SiC) JFET – EliteSiC, Power N-Channel, TO247-4, 1200 V, 7.1 mohm

UF3N120007K4S



TO247-4
CASE 340AN

Description

onsemi's UF3N120007K4S is a 1200 V, 7.1 mΩ High-Performance Gen 3 Normally-On SiC JFET Transistor. This device exhibits Ultra-low On resistance ($R_{DS(ON)}$) in a TO247-4 Package, making it an ideal fit to address the Challenging Thermal Constraints of Solid-state Circuit Breakers and Relay Applications. Additionally, the JFET is a Robust Device Technology Capable of the High-Energy Switching Required in Circuit Protection Applications.

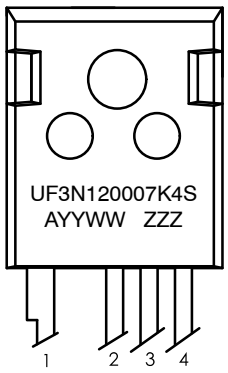
Features

- Single Digit On-Resistance
- Operating Temperature: 175 °C (Max)
- High Pulse Current Capability
- Excellent Device Robustness
- Silver-Sintered Die Attach for Excellent Thermal Resistance
- This Device is Pb-Free, Halogen Free and is RoHS Compliant

Typical Applications

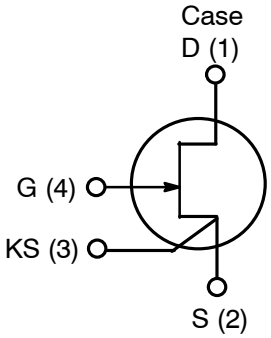
- Solid State / Semiconductor Circuit Breaker
- Solid State / Semiconductor Relay
- Battery Disconnects
- Surge Protection
- Inrush Current Control
- Induction Heating

MARKING DIAGRAM



UF3N120007K4S	= Specific Device Code
A	= Assembly Location
YY	= Year
WW	= Work Week
ZZZ	= Lot ID

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

© Semiconductor Components Industries, LLC, 2024

MAXIMUM RATINGS

Parameter	Symbol	Test Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		1200	V
Gate-Source Voltage	V_{GS}	DC	−30 to +3	V
		AC (Note 1)	−30 to +30	
Continuous Drain Current (Note 2)	I_D	T_C < 112 °C	120	A
Pulsed Drain Current (Note 3)	I_{DM}	T_C = 25 °C	550	A
Power Dissipation	P_{TOT}	T_C = 25 °C	789	W
Maximum Junction Temperature	$T_{J,max}$		175	°C
Operating and Storage Temperature	T_J, T_{STG}		−55 to 175	°C
Max. Lead Temperature for Soldering, 1/8” from Case for 5 seconds	T_L		250	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. +30 V AC Rating Applies for Turn-on Pulses <200 ns applied with external R_G > 1Ω.
2. Limited by Bondwires
3. Pulse width t_p limited by $T_{J,max}$

THERMAL CHARACTERISTICS

Parameter	Symbol	Test Conditions	Value			
			Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$		–	0.15	0.19	°C/W

Share Feedback
Your Opinion Matters

ELECTRICAL CHARACTERISTICS (T_J = +25 °C Unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
TYPICAL PERFORMANCE – STATIC						
Drain-Source Breakdown Voltage	BV_{DS}	V_{GS} = −20 V, I_D = 1 mA	1200	–	–	V
Total Drain Leakage Current	I_{DSS}	V_{DS} = 1200 V, V_{GS} = −20 V, T_J = 25 °C	–	20	300	μA
		V_{DS} = 1200 V, V_{GS} = −20 V, T_J = 175 °C	–	100	–	
Total Gate Leakage Current	I_{GSS}	V_{GS} = −20 V, T_J = 25 °C	–	15	300	μA
		V_{GS} = −20 V, T_J = 175 °C	–	55	–	μA
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 2 V, I_D = 100 A, T_J = 25 °C	–	7.1	–	mΩ
		V_{GS} = 0 V, I_D = 100 A, T_J = 25 °C	–	8.6	11	
		V_{GS} = 2 V, I_D = 100 A, T_J = 175 °C	–	15.5	–	
		V_{GS} = 0 V, I_D = 100 A, T_J = 175 °C	–	17.8	–	
Gate Threshold Voltage	$V_{G(th)}$	V_{DS} = 5 V, I_D = 320 mA	−9.3	−7	−4.7	V
Gate Resistance	R_G	f = 1 MHz, Open Drain	–	0.54	–	Ω
TYPICAL PERFORMANCE – DYNAMIC						
Input Capacitance	C_{iss}	V_{DS} = 800 V, V_{GS} = −20 V, f = 100 kHz	–	8110	–	pF
Output Capacitance	C_{oss}		–	368	–	
Reverse Transfer Capacitance	C_{rss}		–	358	–	
Effective Output Capacitance, Energy Related	$C_{oss(er)}$	V_{DS} = 0 V to 800 V, V_{GS} = −20 V	–	403	–	pF
C_{OSS} Stored Energy	E_{OSS}	V_{DS} = 800 V, V_{GS} = −20 V	–	130	–	μJ
Total Gate Charge	Q_G	V_{DS} = 800 V, I_D = 100 A, V_{GS} = −18 V to 0 V	–	830	–	nC
Gate-Drain Charge	Q_{GD}		–	520	–	
Gate-Source Charge	Q_{GS}		–	120	–	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Share Feedback
Your Opinion Matters

TYPICAL PERFORMANCE DIAGRAM

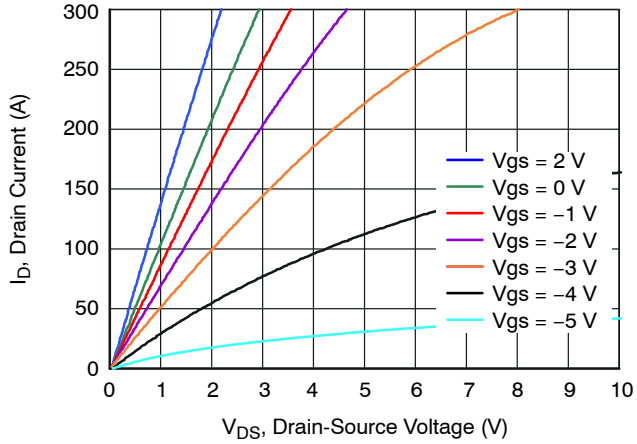


Figure 1. Typical Output Characteristics at T_J = −55 °C, t_p < 250 μs

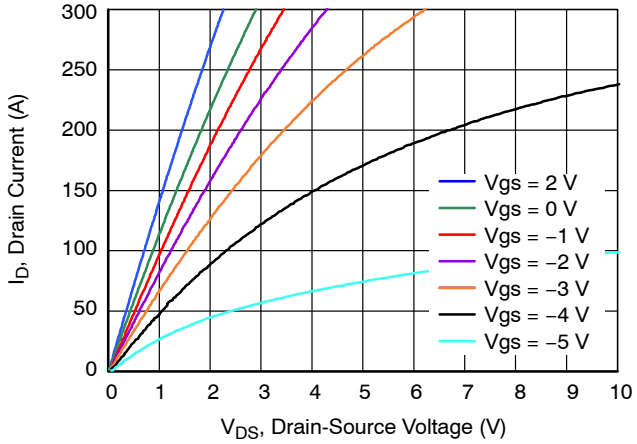


Figure 2. Typical Output Characteristics at T_J = 25 °C, t_p < 250 μs

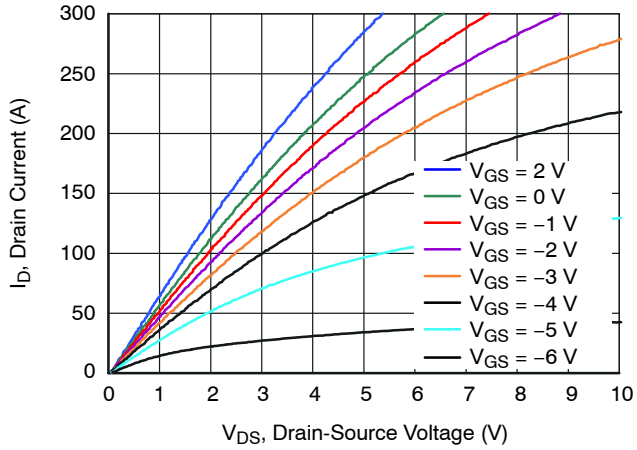


Figure 3. Typical Output Characteristics at T_J = 175 °C, t_p < 250 μs

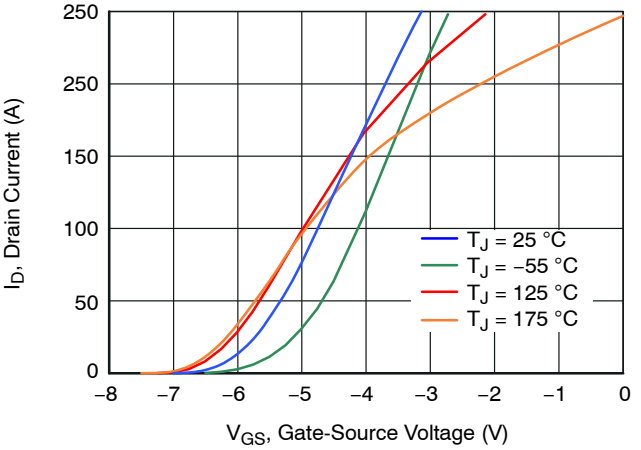


Figure 4. Typical Transfer Characteristics at V_{DS} = 5 V

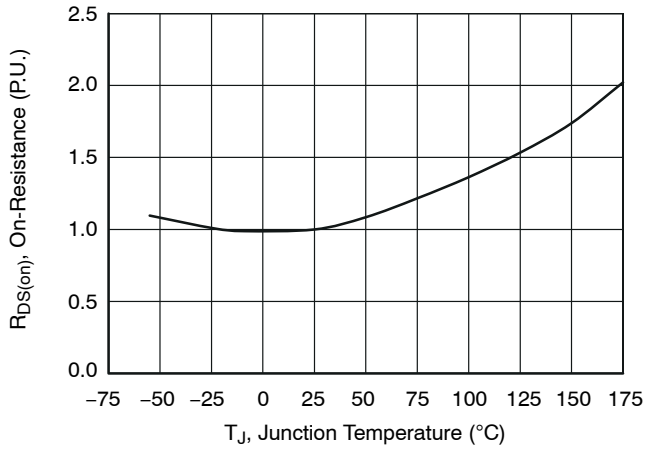


Figure 5. Normalized On-Resistance Vs. Temperature at V_{GS} = 0 V and I_D = 100 A

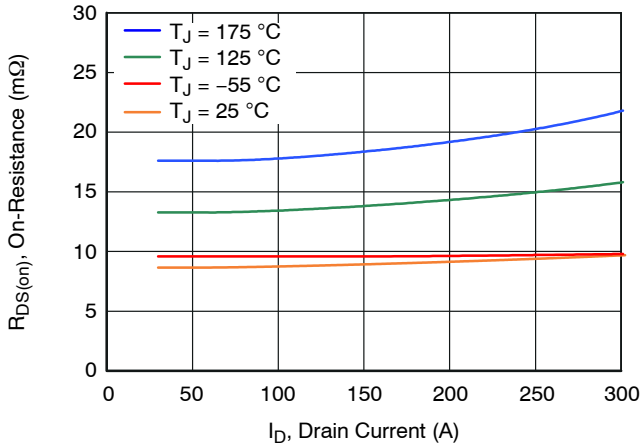


Figure 6. Typical Drain-Source On-Resistance V_{GS} = 0 V

Share Feedback
Your Opinion Matters

TYPICAL PERFORMANCE DIAGRAMS (CONTINUED)

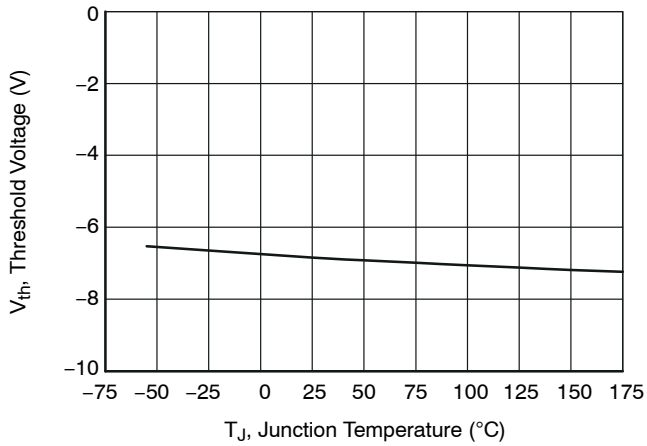


Figure 7. Threshold Voltage vs. Junction Temperature at V_{DS} = 5 V and I_D = 320 mA

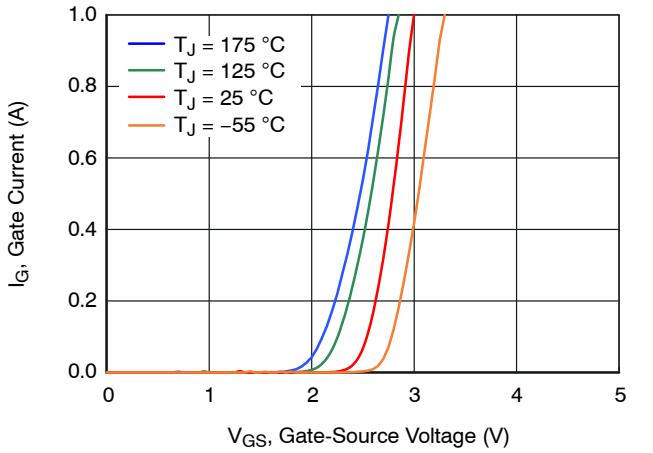


Figure 8. Typical Gate Forward Current at V_{DS} = 0 V

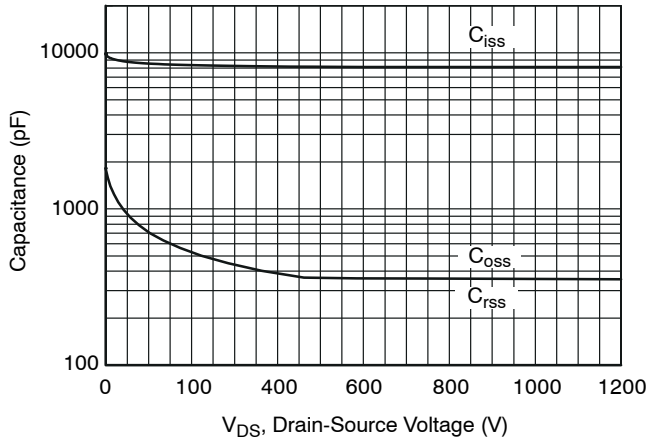


Figure 9. Typical Capacitances at f = 100 KHz and V_{GS} = −20 V

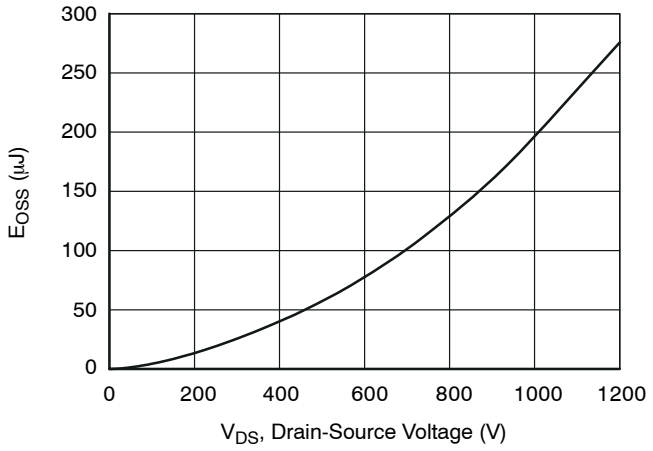


Figure 10. Typical Stored Energy in C_{OSS} at V_{GS} = −20 V

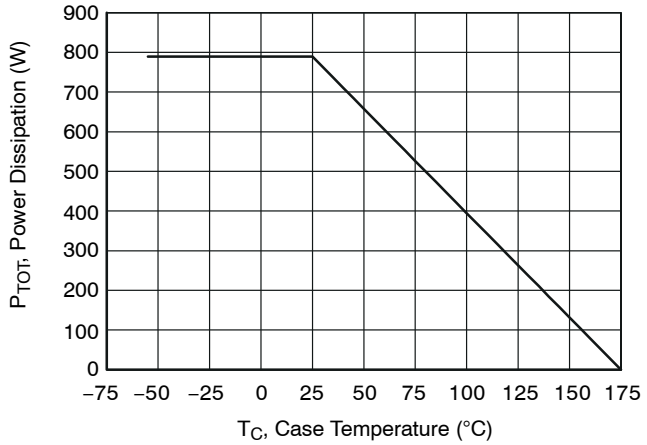


Figure 11. Total Power Dissipation

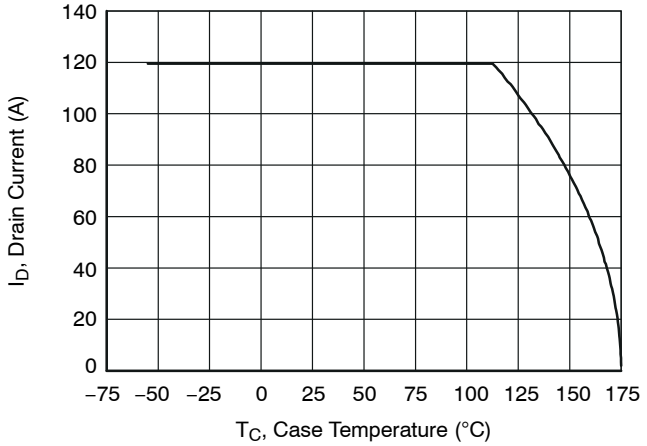


Figure 12. DC Drain Current Derating

Share Feedback
Your Opinion Matters

TYPICAL PERFORMANCE DIAGRAMS (CONTINUED)

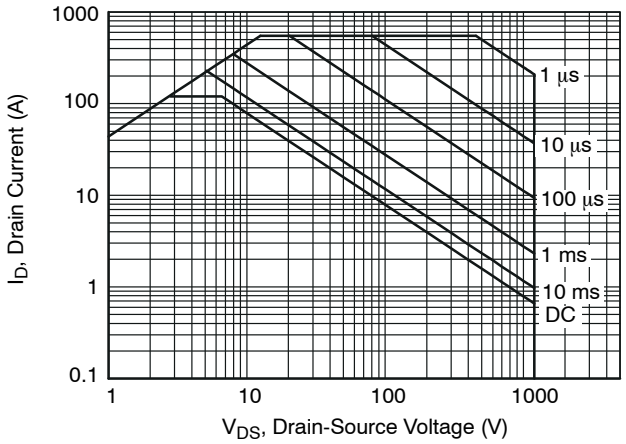
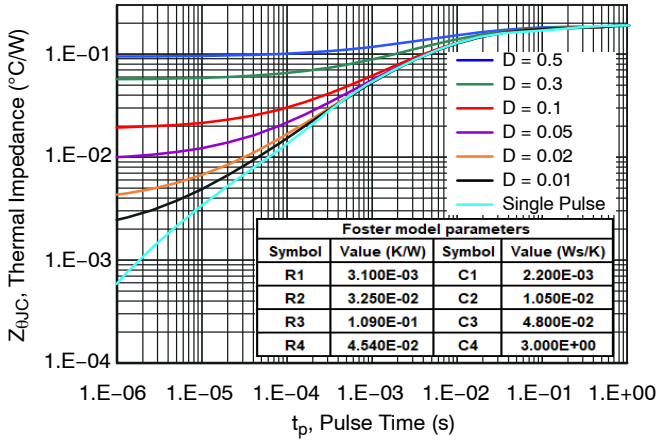


Figure 13. Safe Operation Area at T_C = 25 °C, Parameter t_p



Foster model parameters

Symbol	Value (K/W)	Symbol	Value (Ws/K)
R1	3.100E-03	C1	2.200E-03
R2	3.250E-02	C2	1.050E-02
R3	1.090E-01	C3	4.800E-02
R4	4.540E-02	C4	3.000E+00

Figure 14. Maximum Transient Thermal Impedance

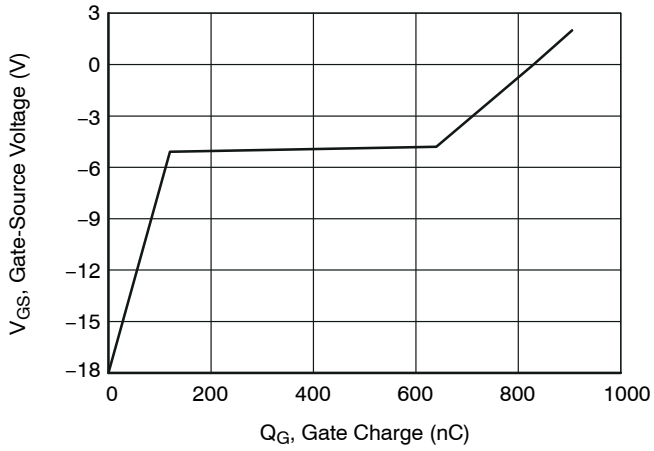
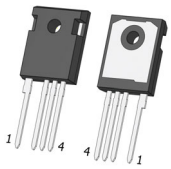


Figure 15. Typical Gate Charge at V_{DS} = 800 V and I_D = 100 A

ORDERING INFORMATION

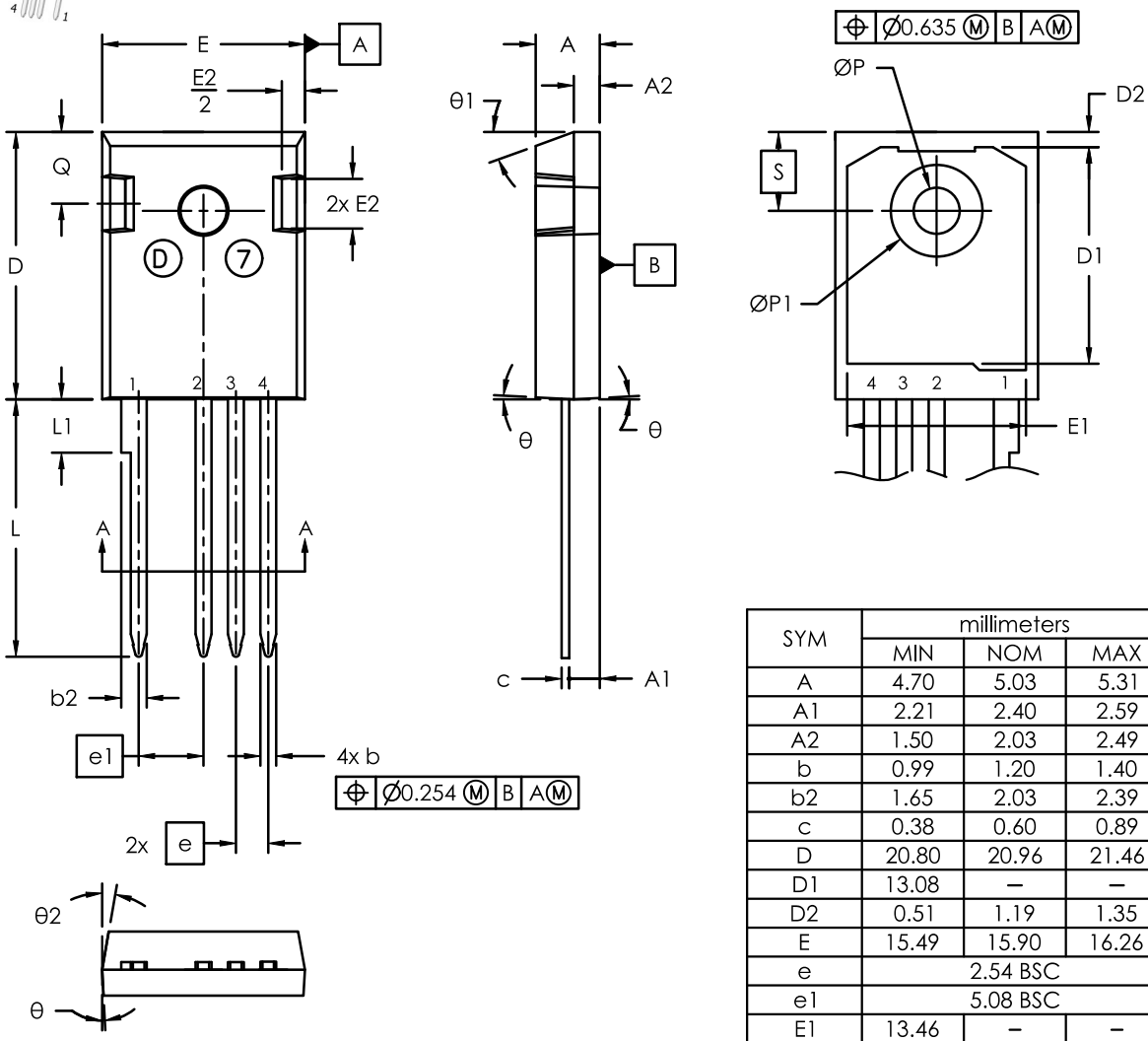
Part Number	Marking	Package	Shipping
UF3N120007K4S	UF3N120007K4S	TO247-4 (Pb−Free, Halogen Free)	600 Units / Tube

Share Feedback
Your Opinion Matters



TO247−4 15.90x20.96x5.03, 5.44P
CASE 340AN
ISSUE E

DATE 20 JUN 2025



SYM	millimeters		
	MIN	NOM	MAX
A	4.70	5.03	5.31
A1	2.21	2.40	2.59
A2	1.50	2.03	2.49
b	0.99	1.20	1.40
b2	1.65	2.03	2.39
c	0.38	0.60	0.89
D	20.80	20.96	21.46
D1	13.08	–	–
D2	0.51	1.19	1.35
E	15.49	15.90	16.26
e	2.54 BSC		
e1	5.08 BSC		
E1	13.46	–	–
E2	3.43	3.89	5.20
L	19.81	20.17	20.32
L1	–	–	4.50
ØP	3.40	3.60	3.80
ØP1	7.06	7.19	7.39
Q	5.38	5.62	6.20
S	6.17 BSC		
θ	3°		
θ1	20°		
θ2	10°		

NOTE:
1. Dimensioning and tolerancing as per ASME Y14.5 - 2018
2. Controlling dimension : millimeters
3. Package Outline in compliance with JEDEC standard var. AD.
4. Dimensions D & E does not include mold flash.
5. ØP to have max draft angle of 1.7° to the top with max. hole diameter of 3.91mm.
5. Through Hole diameter value = End Hole diameter
6. PCB Through Hole pattern as per IPC-2221/IPC-2222

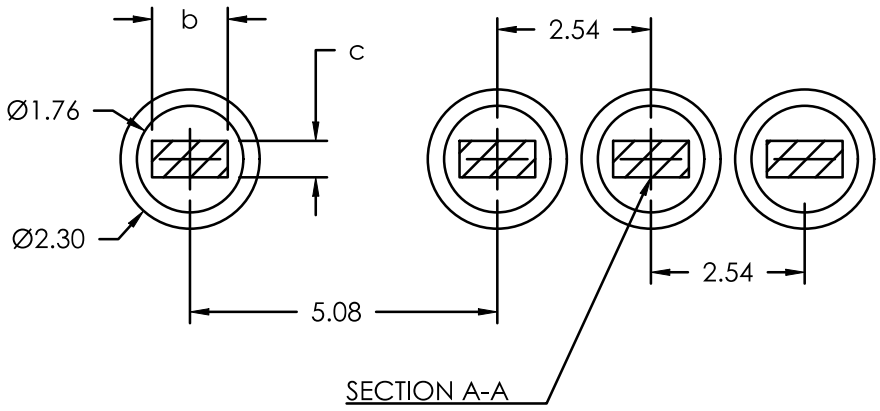
DOCUMENT NUMBER:	**98AON86067F**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	**TO247−4 15.90x20.96x5.03, 5.44P**		**PAGE 1 OF 2**

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

TO247−4 15.90x20.96x5.03, 5.44P
CASE 340AN
ISSUE E

DATE 20 JUN 2025

RECOMMENDED PCB THROUGH HOLE



NOTE: LAND PATTERN AND THROUGH HOLE DIMENSIONS SERVE ONLY AS AN INITIAL GUIDE.
END-USER PCB DESIGN RULES AND TOLERANCES SHOULD ALWAYS PREVAIL.

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

© Semiconductor Components Industries, LLC, 2025

onsemi, ONSEMI , and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent−Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as−is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales